

SPECIFICATION AMENDMENTS

Page 1, replace the paragraph beginning at line 4 to read --

CROSS REFERENCE TO RELATED APPLICATION

This application is a division of Ser. No. 10/066,329
filed 31 January 2002, U.S. Patent 6,730,365 issued 4 May 2004.

Page 5, replace the paragraph beginning at line 15 to read --

The invention utilizes the plasma generated around the substrate and at the substrate holder by the radio frequency or pulsed direct current source connected to the cathodically poled substrate holder to produce a self-bias around and in front of the substrate or substrates which can vary from several [[tons]] tens of volts to many hundreds of volts and usually is at least several hundred volts. The gas which is used can include an inert gas like argon and reactive gases like oxygen and nitrogen or mixtures thereof and the plasma may be maintained at a pressure in the chamber of 10^{-3} to 10^{-2} Torr. The chamber is initially evacuated to about say 10^{-6} Torr before the gas mixture is admitted to the chamber.